

## ABSTRACT

The process of the present invention comprises reactive ion etching of  $\text{Al}_x\text{F}_y\text{O}_z$  oxide deposits on aluminum-containing bond pads using feed gases, such as,  $\text{SF}_6/\text{CF}_4/\text{Ar}$  or  $\text{Cl}_2/\text{BCL}_3/\text{Ar}$ . whose active plasma etches the  $\text{Al}_x\text{F}_y\text{O}_z$  oxide deposits by physical etching and chemical etching for more complete removal of the  $\text{Al}_x\text{F}_y\text{O}_z$  oxide deposits.